

60A,250V 玻璃钝化快恢复二极管
60A,250V Glass Passivated Fast Recovery Diode

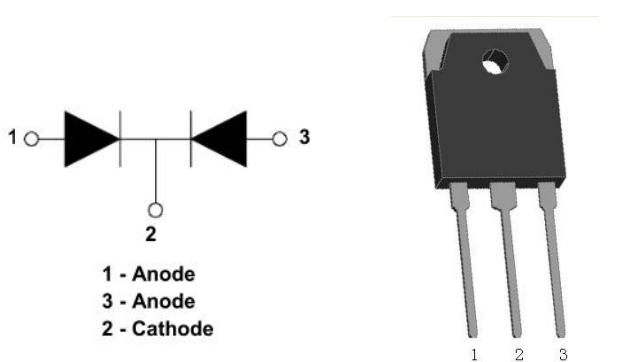
■特征 Features

- 超快恢复时间
Ultra fast Recovery Times
- 软恢复特性
Soft Recovery Characteristics
- 低正向电压
Low Forward Voltage
- 低漏电流
Low Leakage Current

关键参数 KEY PARAMETERS		
参数 PARAMETER	数值 VALUE	单位 UNIT
I _{F(AV)}	60	A
V _{RRM}	250	V
I _{FSM}	800	A
Package	TO-3P	

■应用范围 Applications

- 开关电源
Switch mode Power Supply
- 逆变器
Inverters
- 续流二极管
Free Wheeling Diode
- 电机控制器
Motor Controllers
- 变频器
Converters
- 功率因数校正
PFC



■最大额定值 Maximum Ratings @ Ta = 25°C unless otherwise noted

特征参数/测试条件 Characteristic / Test Conditions		符号 SYMBOL	S2FD60B25 E	单位 UNIT
反向重复峰值电压 Maximum recurrent peak reverse voltage		V _{RRM}	250	V
平均整流输出电流 Average rectified output current	T _C =100°C	I _(AV)	60 (30*2)	A
最大正向浪涌电流, 8.3 ms 单半正弦波叠加在额定负载上 Peak surge forward current, 8.3 ms single half sine-wave superimposed on rated load		I _{FSM}	800	A
结温 Junction temperature		T _j	-55~+150	°C
存储温度 Storage temperature		T _{STG}	-55~+150	°C
结电容 Junction capacitance @4V,1MHz		C _j	800	pF
引脚可承受温度 (10s) Lead Temperature for 10 Sec		T _L	260	°C

■电性特性 Electrical Characteristics @ $T_a = 25^\circ\text{C}$ unless otherwise noted

参数 PARAMETER	条件 CONDITIONS	符号 SYMBOL	标准值 Typ	最大值 Max	单位 UNIT
正向峰值电压 Peak Forward Voltage	IF=30.0A, $T_j=25^\circ\text{C}$	V_F	0.93	1.0	V
	IF=30.0A, $T_j=125^\circ\text{C}$		0.78	0.83	V
反向峰值电流 Peak Reverse Current	VR=VRRM, 脉冲测试, 单个二极管的额定值 VR=VRRM, Pulse measurement, Rating of per diode	I_R	/	5	μA
			/	100	
反向恢复时间 Reverse Recovery Time	IF=0.5A, $IRM=1\text{A}$, $IRR=0.25\text{A}$, $TC=25^\circ\text{C}$	Tr	48	50	ns

■热特性 Thermal Characteristics @ $T_a = 25^\circ\text{C}$ unless otherwise noted

参数 PARAMETER	符号 SYMBOL	额定值 RATED VALUE	单位 UNIT
结到壳体的热阻, 带散热器 Junction-to-case thermal resistance with heat sink	$R_{\theta Jc}$	0.8	$^\circ\text{C}/\text{W}$

■特性曲线 Characteristic Curve

FIG.1 . Derating Curve For Output Rectified Current

图 1. 电流降额曲线

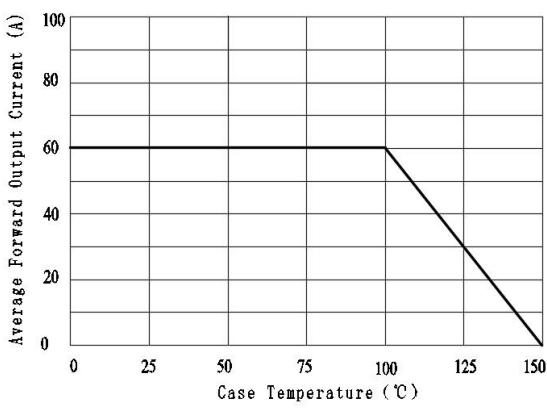


FIG.2 . Maximum Non-Repetitive Peak Forward Surge Current Per Bridge Element

图 2. 最大正向不重复峰值浪涌电流

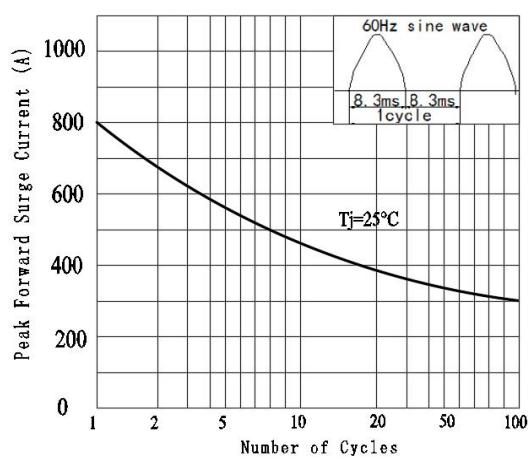


FIG.3.Typical Reverse Characteristics Per Bridge Element

图 3. 典型反向特性

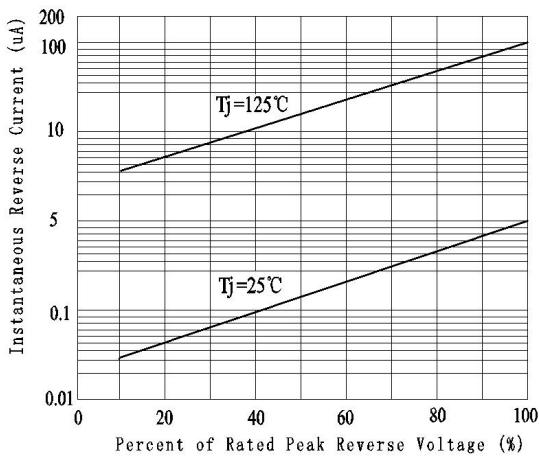


FIG.4.Typical Forward Characteristics Per Bridge Element

图 4. 典型正向特性

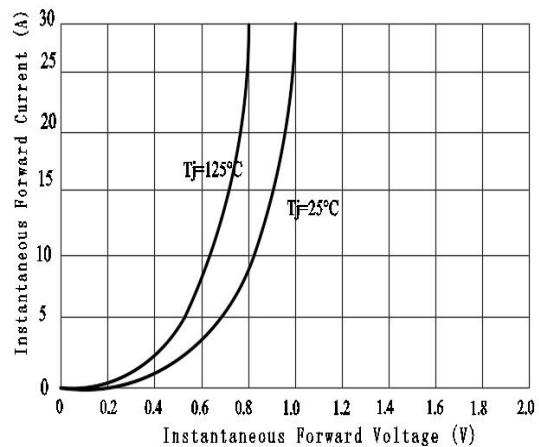
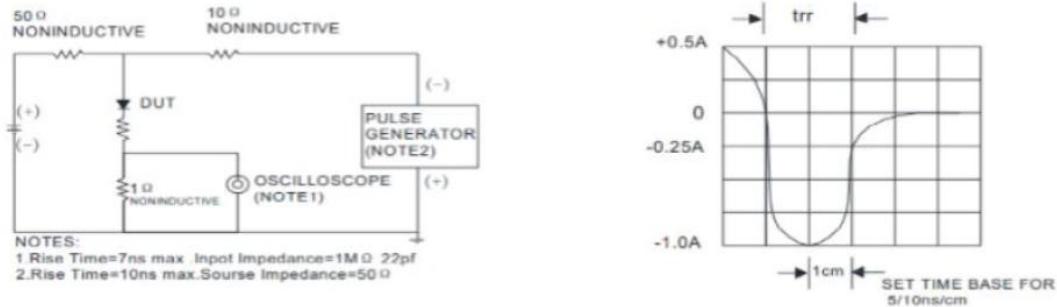


FIG.5. Diode Reverse Recovery Test Circuit and Waveform

图 5. 二极管反向恢复测试电路及波形



■标记图 Marking Diagram

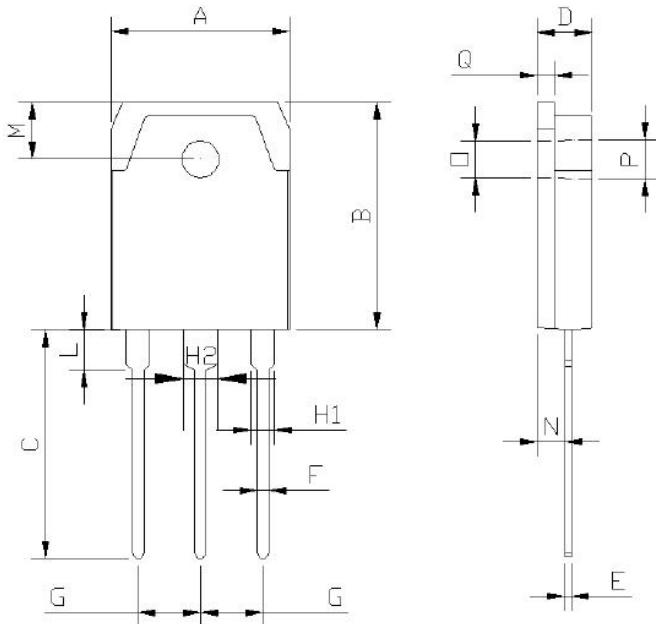


: 希尔LOGO

S2FD60B25 E: 标识代码

NHA001: 产品批次码

■尺寸图 Dimension Drawing



Dim.	Millimeter		Inches	
	min	max	min	max
A	15.1	16.1	0.594	0.634
B	19.4	20.4	0.764	0.803
C	19	20	0.748	0.787
D	4.3	5.3	0.169	0.209
E	0.4	0.8	0.016	0.031
F	0.8	1.2	0.031	0.047
G	5.25	5.65	0.207	0.222
H1	1.8	2.2	0.071	0.087
H2	2.8	3.2	0.110	0.126
L	2.7	3.1	0.106	0.122
M	4.7	5.3	0.185	0.209
N	2.2	2.6	0.087	0.102
O	3	3.3	0.118	0.130
P	3.3	3.6	0.130	0.142

Notice

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